

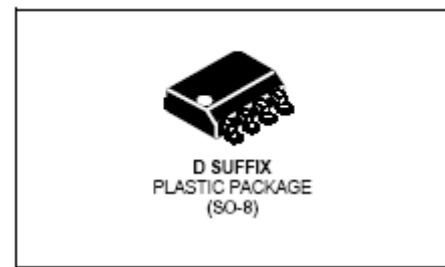
ISO K Line Serial Link Interface

IL33290

The IL33290 is a serial link bus interface device designed to provide bidirectional half-duplex communication interfacing in automotive diagnostic applications. It is designed to interface between the vehicle's on-board microcontroller and systems off-board the vehicle via the special ISO K line.

The IL33290 is designed to meet the Diagnostic Systems ISO9141 specification. The device's K line bus driver's output is fully protected against bus shorts and overtemperature conditions.

The IL33290 derives its robustness to temperature and voltage extremes by being built on a process, incorporating CMOS logic, bipolar/MOS analog circuitry, and DMOS power FETs. Although the IL33290 was principally designed for automotive applications, it is suited for other serial communication applications. It is parametrically specified over an ambient temperature range of $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$ and $8.0\text{ V} \leq V_{\text{BB}} \leq 18\text{ V}$ supply. The economical SO-8 surface-mount plastic package makes the IL33290 very cost effective.



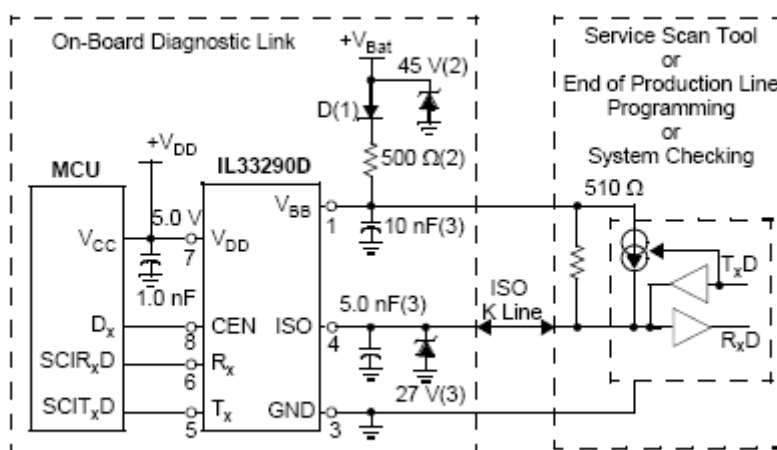
ORDERING INFORMATION

Device	Temperature Range (T _A)	Package
IL33290D	-40 to 125°C	SO-8

Features

- Designed to Operate Over Wide Supply Voltage of 8.0 to 18 V
- Ambient Operating Temperature of -40 to 125°C
- Interfaces Directly to Standard CMOS Microprocessors
- ISO K Line Pin Protected Against Shorts to Ground
- Thermal Shutdown with Hysteresis
- Maximum Transmission Speeds in Excess of 50 k Baud
- ISO K Line Pin Capable of High Currents
- ISO K Line Can Be Driven with up to 10 nF of Parasitic Capacitance
- 8.0 kV ESD Protection Attainable with Few Additional Components
- Standby Mode: No V_{Bat} Current Drain with V_{DD} at 5.0 V
- Low Current Drain During Operation with V_{DD} at 5.0 V

IL33290D Simplified Application Diagram



Components necessary for Reverse Battery (1), Overvoltage Transient (2), and 8.0 kV ESD Protection (3) in a metal module case. This device contains 85 active transistors.

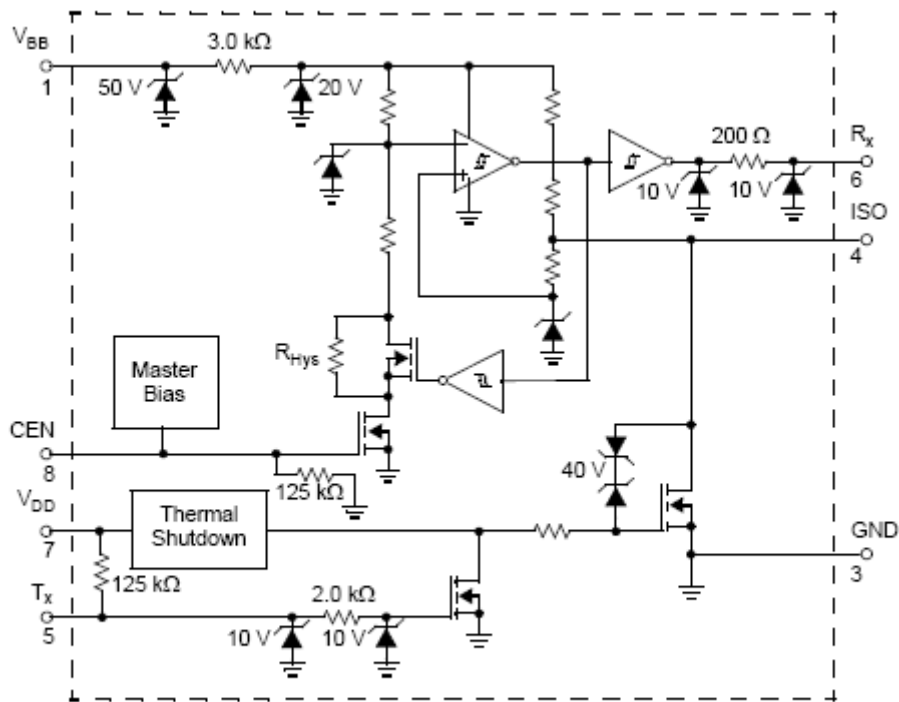
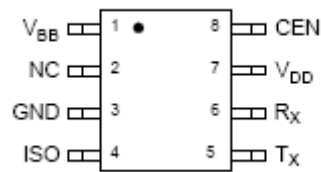


Figure 1. IL33290D Simplified Block Diagram



Pin Function Description

Pin Number	Pin Name	Description
1	V _{BB}	Battery power through external resistor and diode.
2	NC	Not to be connected. (Note 1)
3	GND	Common signal and power return.
4	ISO	Bus connection.
5	T _X	Logic level input for data to be transmitted on the bus.
6	R _X	Logic output of data received on the bus.
7	V _{DD}	Logic power source input.
8	CEN	Chip enable. Logic "1" for active state. Logic "0" for sleep state.

Notes

1. NC pins should not have any connections made to them. NC pins are not guaranteed to be open circuits.

Maximum Ratings

All voltages are with respect to ground unless otherwise noted.

Rating	Symbol	Value	Unit
V _{DD} DC Supply Voltage	V _{DD}	-0.3 to 7.0	V
V _{BB} Load Dump Peak Voltage	V _{BB(LD)}	45	V
ISO Pin Load Dump Peak Voltage (Note 2)	V _{ISO}	40	V
ISO Short Circuit Current Limit	I _{ISO(LIM)}	1.0	A
ESD Voltage (Note 3) Human Body Model (Note 4) Machine Model (Note 5)	V _{ESD1} V _{ESD2}	2000 200	V
ISO Clamp Energy (Note 6)	E _{clamp}	10	mJ
Storage Temperature	T _{stg}	-55 to +150	°C
Operating Case Temperature	T _C	-40 to +125	°C
Operating Junction Temperature	T _J	-40 to +150	°C
Power Dissipation T _A = 25°C	P _D	0.8	W
Lead Soldering Temperature (Note 7)	T _{solder}	260	°C
Thermal Resistance Junction-to-Ambient	R _{θJA}	150	°C/W

Notes

- Device will survive double battery jump start conditions in typical applications for 10 minutes duration, but is not guaranteed to remain within specified parametric limits during this duration.
- ESD data available upon request.
- ESD1 testing is performed in accordance with the Human Body Model (C_{ZAP} = 100 pF, R_{ZAP} = 1500 Ω).
- ESD2 testing is performed in accordance with the Machine Model (C_{ZAP} = 200 pF, R_{ZAP} = 0 Ω).
- Nonrepetitive clamping capability at 25°C.
- Lead soldering temperature limit is for 10 seconds maximum duration.

* Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Static Electrical Characteristics

Characteristics noted under conditions of $4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$, $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$, $-40^\circ\text{C} \leq T_C \leq 125^\circ\text{C}$, unless otherwise noted.

Characteristic	Symbol	Min	Typ	Max	Unit
POWER AND CONTROL					
V_{DD} Sleep State Current $T_X = 0.8 V_{DD}$, $CEN = 0.3 V_{DD}$	$I_{DD(SS)}$	–	–	0.1	mA
V_{DD} Quiescent Operating Current $T_X = 0.2 V_{DD}$, $CEN = 0.7 V_{DD}$	$I_{DD(Q)}$	–	–	1.0	mA
V_{BB} Sleep State Current $V_{BB} = 16\text{ V}$, $T_X = 0.8 V_{DD}$, $CEN = 0.3 V_{DD}$	$I_{BB(SS)}$	–	–	50	μA
V_{BB} Quiescent Operating Current $T_X = 0.2 V_{DD}$, $CEN = 0.7 V_{DD}$	$I_{BB(Q)}$	–	–	1.0	mA
Chip Enable Input High-Voltage Threshold (Note 8) Input Low-Voltage Threshold (Note 9)	$V_{IH(CEN)}$ $V_{IL(CEN)}$	$0.7 V_{DD}$ –	– –	– $0.3 V_{DD}$	V
Chip Enable Pull-Down Current (Note 10)	$I_{PD(CEN)}$	2.0	–	40	μA
T_X Input Low-Voltage Threshold $R_{ISO} = 510\ \Omega$ (Note 11)	$V_{IL(TX)}$	–	–	$0.3 \times V_{DD}$	V
T_X Input High-Voltage Threshold $R_{ISO} = 510\ \Omega$ (Note 12)	$V_{IH(TX)}$	$0.7 \times V_{DD}$	–	–	V
T_X Pull-Up Current (Note 13)	$I_{PU(TX)}$	-40	–	-2.0	μA
R_X Output Low-Voltage Threshold $R_{ISO} = 510\ \Omega$, $T_X = 0.2 V_{DD}$, R_X Sinking 1.0 mA	$V_{OL(RX)}$	–	–	$0.2 V_{DD}$	V
R_X Output High-Voltage Threshold $R_{ISO} = 510\ \Omega$, $T_X = 0.8 V_{DD}$, R_X Sourcing 250 μA	$V_{OH(RX)}$	$0.8 V_{DD}$	–	–	V
Thermal Shutdown (Note 14)	T_{LIM}	150	170	–	$^\circ\text{C}$

Notes

8. When I_{BB} transitions to $>100\ \mu\text{A}$.
9. When I_{BB} transitions to $<100\ \mu\text{A}$.
10. Enable pin has an internal current pull-down equivalent to greater than 50 k Ω .
11. Measured by ramping T_X down from $0.7 V_{DD}$ and noting T_X value at which ISO falls below $0.2 V_{BB}$.
12. Measured by ramping T_X up from $0.3 V_{DD}$ and noting the value at which ISO rises above $0.9 V_{BB}$.
13. T_X pin has internal current pull-up equivalent to greater than 50 k Ω . Pull-Up current measured with T_X pin at $0.7 V_{DD}$.
14. Thermal Shutdown performance (T_{LIM}) is guaranteed by design but not production tested.

Static Electrical Characteristics (continued)

Characteristics noted under conditions of $4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$, $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$, $-40^\circ\text{C} \leq T_C \leq 125^\circ\text{C}$, unless otherwise noted.

Characteristic	Symbol	Min	Typ	Max	Unit
ISO I/O					
Input Low Voltage Threshold $R_{ISO} = 0\ \Omega$, $T_X = 0.8\ V_{DD}$ (Note 15)	$V_{IL(ISO)}$	–	–	$0.4 \times V_{BB}$	V
Input High Voltage Threshold $R_{ISO} = 0\ \Omega$, $T_X = 0.8\ V_{DD}$ (Note 16)	$V_{IH(ISO)}$	$0.7 \times V_{BB}$	–	–	V
Input Hysteresis (Note 17)	$V_{Hys(ISO)}$	$0.05 \times V_{BB}$	–	$0.1 \times V_{BB}$	V
Internal Pull-Up Current $R_{ISO} = \infty\ \Omega$, $T_X = 0.8\ V_{DD}$, $V_{ISO} = 9.0\text{ V}$, $V_{BB} = 18\text{ V}$	$I_{PU(ISO)}$	-5.0	–	-120	μA
Short Circuit Current Limit (Note 18) $R_{ISO} = 0\ \Omega$, $T_X = 0.4\ V_{DD}$, $V_{ISO} = V_{BB}$	$I_{SC(ISO)}$	50	–	1000	mA
Output Low Voltage $R_{ISO} = 510\ \Omega$, $T_X = 0.2\ V_{DD}$	$V_{OL(ISO)}$	–	–	$0.1 \times V_{BB}$	V
Output High Voltage $R_{ISO} = \infty\ \Omega$, $T_X = 0.8\ V_{DD}$	$V_{OH(ISO)}$	$0.95 \times V_{BB}$	–	–	V

Notes

15. ISO ramped from $0.8\ V_{BB}$ to $0.4\ V_{BB}$, Monitor RX, Value of ISO voltage at which R_X transitions to $0.3\ V_{DD}$.
16. ISO ramped from $0.4\ V_{BB}$ to $0.8\ V_{BB}$, Monitor RX, Value of ISO voltage at which R_X transitions to $0.7\ V_{DD}$.
17. Input Hysteresis, $V_{Hys(ISO)} = V_{IH(ISO)} - V_{IL(ISO)}$.
18. ISO has internal current limiting.

Dynamic Electrical Characteristics

Characteristics noted under conditions of $4.75\text{ V} \leq V_{DD} \leq 5.25\text{ V}$, $8.0\text{ V} \leq V_{BB} \leq 18\text{ V}$, $-40^\circ\text{C} \leq T_C \leq 125^\circ\text{C}$, unless otherwise noted.

Characteristic	Symbol	Min	Typ	Max	Unit
Fall Time (Note 19) $R_{ISO} = 510\ \Omega$ to V_{BB} , $C_{ISO} = 10\text{ nF}$ to Ground	$t_{fall(ISO)}$	–	–	2.0	μs
ISO Propagation Delay (Note 20) High to Low: $R_{ISO} = 510\ \Omega$, $C_{ISO} = 500\text{ pF}$ (Note 21) Low to High: $R_{ISO} = 510\ \Omega$, $C_{ISO} = 500\text{ pF}$ (Note 22)	$t_{PD(ISO)}$	– –	– –	2.0 2.0	μs

Notes

19. Time required ISO voltage to transition from $0.8 V_{BB}$ to $0.2 V_{BB}$.

20. Changes in the value of CISO affect the rise and fall time but have minimal effect on Propagation Delay.

21. Step T_X voltage from $0.2 V_{DD}$ to $0.8 V_{DD}$. Time measured from $V_{IH(ISO)}$ until V_{ISO} reaches $0.3 V_{BB}$.

22. Step T_X voltage from $0.8 V_{DD}$ to $0.2 V_{DD}$. Time measured from $V_{IL(ISO)}$ until V_{ISO} reaches $0.7 V_{BB}$.

Application Information

INTRODUCTION

The IL33290D is a serial link bus interface device conforming to the ISO 9141 physical bus specification. The device was designed for automotive environment usage compliant with On-Board Diagnostic (OBD) requirements set forth by the California Air Resources Board (CARB) using the ISO K line. The device does not incorporate an ISO L line. It provides bi-directional

half-duplex communications interfacing from a microcontroller to the communication bus. The IL33290D incorporates circuitry to interface the digital translations from 5.0 V microcontroller logic levels to battery level logic and from battery level logic to 5.0 V logic levels. The IL33290D is packaged in an 8-pin plastic SOIC.

FUNCTIONAL DESCRIPTION

The IL33290D transforms 5.0 V microcontroller logic signals to battery level logic signals and visa versa. This serial link interface device, operating in a typical automotive diagnostic application, operates at bit rates up to 10.4 kbps with less than 2.0 μ s propagation delay and less than 2.0 μ s fall time. Rise time is a function of the resistor used in the application to pull up the bus to battery voltage, working in conjunction with the total capacitance present on the bus. The serial link interface will remain fully functional over a battery voltage range of 6.0 to 18 V. The device is parametrically specified over a dynamic V_{BB} voltage range of 8.0 to 18 V.

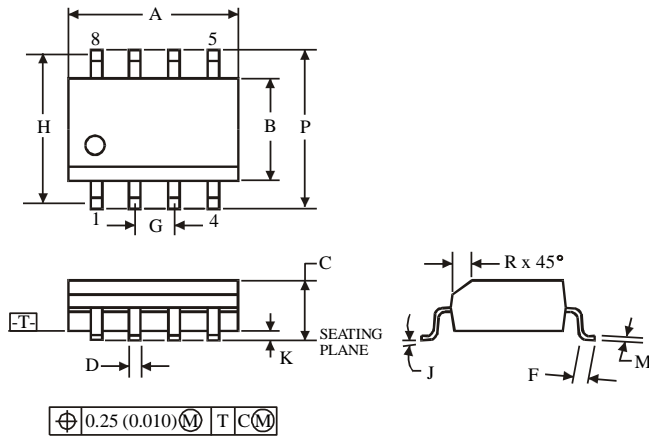
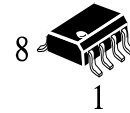
Required input levels from the microcontroller are ratio-metric with the V_{DD} voltage normally used to power the microcontroller. This enhances the ability to remain in harmony with the R_x and T_x control input signals of the microcontroller. The R_x and T_x control inputs are compatible with standard 5.0 V CMOS circuitry. For fault-tolerant purposes the T_x input from the microcontroller has an internal passive pull-up to V_{DD} of approximately 125 k Ω , while the CEN input has an internal passive pull-down to ground of approximately 125 k Ω .

In the receive mode, all ISO K Line bus input signals greater than the $0.7 \times V_{BB}$ thresholds are valid for a high-level signal and less than the $0.4 \times V_{BB}$ thresholds for a low-level signal. In the transmit mode, valid ISO K line bus output signal levels are greater than $0.95 \times V_{BB}$ and less than $0.1 \times V_{BB}$. A pull-up resistor of ≥ 100 k Ω to battery is internally provided as well as an active data pull-down. The internal active pull-down is current-limit-protected against shorts to battery and further protected by thermal shutdown. Typical applications have reverse battery protection by the incorporation of an external 510 Ω pull-up resistor and diode to battery.

Reverse battery protection of the device is provided by using a reverse battery blocking diode [(D) in the Simplified Application Diagram on page 1]. Battery line transient protection of the device is provided for by using a 45 V zener and a 500 Ω resistor connected to the V_{BB} source as shown in the same diagram. Device ESD protection from the communication lines exiting the module is through the use of the 10 nF connected to the V_{BB} device pin and the 5.0 nF used in conjunction with the 27 V zener connected to the ISO pin.

Package Dimensions

D SUFFIX SOIC
(MS - 012AA)



Symbol	Dimension, mm	
	MIN	MAX
A	4.80	5.00
B	3.80	4.00
C	1.35	1.75
D	0.33	0.51
F	0.40	1.27
G	1.27	
H	5.72	
J	0°	8°
K	0.10	0.25
M	0.19	0.25
P	5.80	6.20
R	0.25	0.50

NOTES:

1. Dimensions A and B do not include mold flash or protrusion.
2. Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B - 0.25 mm (0.010) per side.